- 1. A method of increasing the efficiency of a luminescent material having
- 2 current carriers with a spin flip rate, an emissive singlet recombination channel, and a non-emissive triplet recombination channel, and wherein the singlet recombination cross
- 4 section is greater than the triplet recombination cross section, the method comprising:

processing the luminescent material so as to increase the spin flip rate of the

- 6 current carriers.
- 2. The method of claim 1, wherein the processing includes adding an
- 2 impurity to the luminescent material.
 - 3. The method of claim 1, wherein the processing includes a magnetic field.
- 4. The method of claim 1, wherein the processing includes an increase in
- 2 effective spin temperature.
 - 5. The method of claim 1, wherein the material is a polymer.
 - 6. The method of claim 1, wherein the material is an oligomer
 - 7. The method of claim 1, wherein the material is a molecular crystal.
 - 8. The method of claim 1, wherein the material is a fullerene.

- 9. The method of claim 1, wherein the impurity is magnetically active.
- 10. The method of claim 1, wherein the impurity is a paramagnetic.
- 11. The method of claim 1, wherein the impurity facilitates low-frequency
- 2 vibrations.
 - 12. A light-emitting device incorporating the material of claim 1.
 - 13. A method of improving the efficiency of an organic light-emitting material
- 2 having carriers which exhibit a spin-lattice relaxation rate, the method comprising:

adding an impurity to the material so as to increase the spin-lattice relaxation rate

- 4 of the carriers.
 - 14. The method of claim 13, wherein the material is a polymer.
 - 15. The method of claim 13, wherein the material is an oligomer.
 - 16. The method of claim 13, wherein the material is a molecular crystal.
 - 17. The method of claim 13, wherein the material is a fullerene.

- 18. The method of claim 13, wherein the impurity is magnetically active.
- 19. The method of claim 13, wherein the impurity is a paramagnetic.
- 20. The method of claim 13, wherein the impurity facilitates low-frequency
- 2 vibrations.
 - 21. A light-emitting device incorporating the material of claim 13.
- 22. An material for use in a high-efficiency light-emitting device, the material
- 2 comprising:

an electro-luminescent compound in which useful light emission occurs only

4 through the recombination of singlet excitons; and

an impurity, added so as to increase the spin flip rate of carriers propagating

- 6 through the material.
 - 23. An electro-luminescent device, comprising:
- 2 a first electrode;

an electro-luminescent layer supporting the flow of current carriers having a spin-

4 flip rate;

a second electrode; and

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an organic electro-luminescent material and an impurity added the electroluminescent layer so as to increase the spin flip rate of the current carriers.

24. A laser, comprising:

- a light-emissive layer from which light is emitted through the injection of current carriers having a spin-flip rate;
- 4 an optical resonator;

an organic electro-luminescent material and an impurity added to the light-

6 emissive layer so as to increase the spin flip rate of the current carriers.